Title of the Invention: Chemical Mechanical Abrasive Composition for Use in Semiconductor Processing

Abstract of the Disclosure

The invention provides a chemical-mechanical abrasive composition for semiconductor processing, which composition is characterized by comprising a water-soluble anionic chemical. According to the invention, said water-soluble anionic chemical would be coated on the surface of a metal film during the polishing of said metal film so as to inhibit the formation of depressions on the resultant metal circuits.

In another aspect, the invention provides a chemical-mechanical abrasive composition in the form of a slurry comprising 70-99.5% by weight of an aqueous medium; 0.1-25% by weight of an abrasive particle; 0.01-2.0% by weight of an abrasion enhancer; and 0.01-1% by weight of a water-soluble anionic chemical. The chemical-mechanical abrasive composition of the invention may further comprise an oxidant to enhance the abrasion rate.

(FIGURE 1 IS SUGGESTED FOR PUBLICATION)